



REPLACEMENT ABSTRACT

A semiconductor device is disclosed, which ~~comprises~~ includes a semiconductor substrate, a multilayer metal wiring layer, a capacitor comprising first and second elements, each element including a lower metal electrode, a dielectric film, and an upper metal electrode ~~stacked~~ formed on the multilayer metal wiring layer, and first and second wiring layers of an upper layer formed on an insulation film which covers the capacitor, wherein the upper metal electrodes have the same size and shape, the upper metal electrode of each element is provided within an area in which the lower metal electrode and the dielectric film of the each element are stacked, and the lower metal electrode of the first element and the upper metal electrode of the second element are connected to each other, and the upper metal electrode of the first element and the lower metal electrode of the second element are connected to each other.